NSN 5961-01-226-8502

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Inclosure Material:
Glass
Overall Length:
0.357 inches
Terminal Length:
1.000 inches
Overall Diameter:
0.235 inches
Function For Which Designed:
Transient suppressor
End Application:
Over the horizon back scanner; los angeles class ssn (688); nimitz class cvn; arleigh burke class ddg; seawolf class ssn; emory s. Land
class as; supply class aoe; submarine interior comm system; sub comm and antenna systems
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
Do-13
Mounting Method:
Terminal
Features Provided:
Hermetically sealed case
Criticality Code Justification:
Feat
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
15.8 reverse breakdown voltage, dc
Current Rating Per Characteristic:
1.00 milliamperes forward current, average torr
Power Rating Per Characteristic:
1.0 watts small-signal input power, common-collector major
Maximum Operating Tempurature Per Measurement Point:
175.0 degrees celsius ambient air
Special Features:
Weapon system essential; junction pattern arrangement: pn
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
2 uninsulated wire lead
Specification Data:
81349-mil-s-19500/507 government specification
Shelf Life:
N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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